



First Named Inventor	Leonard Forbes
Serial No.	10/775,908
Filing Date	February 10, 2004
Group Art Unit	2818
Examiner Name	Unknown
Confirmation No.	1212
Attorney Docket No.	400.272US01
Title: NROM FLASH MEMORY WITH A HIGH-PERMITTIVITY GATE DIELECTRIC	

I-1

**GENERAL
TRANSMITTAL
FORM UNDER 37 CFR 1.8
(LARGE ENTITY)**

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Enclosures

The following documents are enclosed:

Information Disclosure Statement (1 pg.); Form 1449 (7 pgs.); 58 copies of cited references; U.S. reference(s) not included pursuant to 37 C.F.R. 1.98 (c)(2)(i);
 An itemized return-receipt postcard

Leffert Jay & Polglaze, P.A.
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Submitted By

Name	Kenneth W. Bolvin	Reg. No.	34,125	Telephone	(612) 312-2211
Signature				Date	8/31/04

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Name	Rhonda L. Foley	Signature	
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(LARGE ENTITY TRANSMITTAL UNDER 37 CFR § 1.8)



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INFORMATION DISCLOSURE STATEMENT

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In compliance with 37 C.F.R. §§ 1.56 and 1.97, *et seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application.

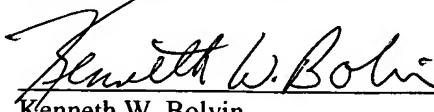
Pursuant to 37 C.F.R. 1.98 (a)(2)(i), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Applications. Applicant respectfully requests that this Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

As an Office Action has not yet issued in this application, Applicant believes that no fees are due. However, the Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373.

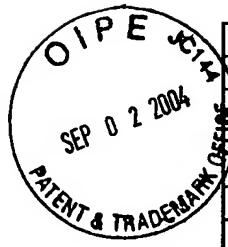
If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211.

Respectfully submitted,

Date: 8/31/04


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